

GaAs MMIC 6-BIT DIGITAL PHASE SHIFTER, 1.2 - 1.6GHz

Features

Freq: $1.2{\sim}1.6\text{GHz}$

360°Coverage, LSB = 5.625°

RMS Phase Error: 1° Insertion Loss: 5 dB Supply Voltage: -5V Control Voltage: 0/+5V

Chip Size: 3.8mm×1.24mm×0.1mm

General Description

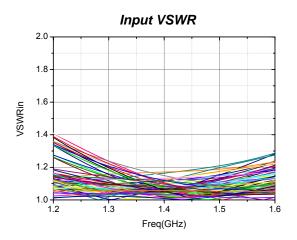
The HG162YA is a 6-bit GaAs pHEMT digital phase shifter which is rated from 1.2 to 1.6 GHz, providing 360 degrees of phase coverage, with a LSB of 5.625 degrees. The phase shifter features very low RMS phase error of 1 degrees and extremely low insertion loss of 5dB across all phase states. This high accuracy phase shifter is controlled with positive logic of 0/+5V, and requires -5V bias supply.

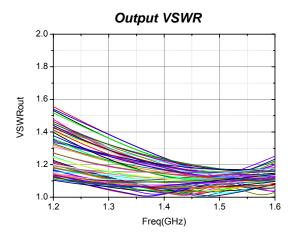
Electrical Specifications(T_A =25 C, Vdd= -5V)

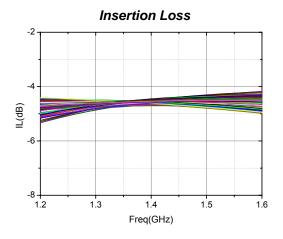
| Parameter | Min. | Тур. | Max. |
|-------------------------|---------|--------|------|
| Frequency Range(GHz) | 1.2~1.6 | | |
| Input VSWR | - | 1.2 | - |
| Output VSWR | - | 1.4 | - |
| Insertion Loss(dB) | - | 5 | - |
| Amplitude Variation(dB) | - | ±0.5 | - |
| Phase Error(°) | - | -1.5~4 | - |
| RMS Phase Error(°) | - | 1 | - |

Truth Table(0: 0V, 1: +5V)

| State | PC1 | PC2 | PC3 | PC4 | PC5 | PC6 |
|-----------|-----|-----|-----|-----|-----|-----|
| 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| -5.625° | 1 | 0 | 0 | 0 | 0 | 0 |
| -11.25° | 0 | 1 | 0 | 0 | 0 | 0 |
| -22.5° | 0 | 0 | 1 | 0 | 0 | 0 |
| -45° | 0 | 0 | 0 | 1 | 0 | 0 |
| -90° | 0 | 0 | 0 | 0 | 1 | 0 |
| -180° | 0 | 0 | 0 | 0 | 0 | 1 |
| -354.375° | 1 | 1 | 1 | 1 | 1 | 1 |

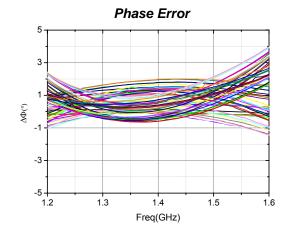


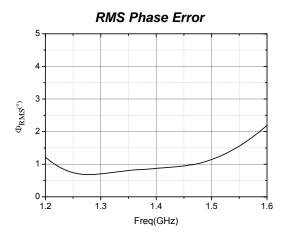


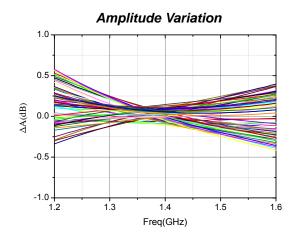




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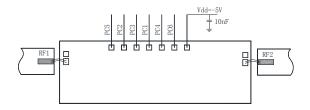




Outline Drawing (mm)



Assembly Diagram



Absolute Maximum Ratings

| Supply Voltage | -5.5V | | |
|-----------------------|----------------------|-----------------------|--|
| RF Input Power | +27dBm | | |
| Control Voltage | Low Level: 0~0.5V | High Level: 3.7~5V | |
| Operating Temperature | -55℃∼125℃ | | |
| Storage Temperature | -65℃~150℃ | | |

Notes:

- 1. The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
- 2. GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
- 3. The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300° C, and no more than 30 sec.), and should make it fully grounded.
- 4.The chip microwave port and substrate gap is not exceeding 0.05mm, with $\Phi25\mu m$ double gold wire bonding, suggested length of gold wire 250 $\sim\!400\mu m.$
- 5. Chip microwave port without DC blocking capacitor.
- 6. The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.